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	Filing Date		2006-06-22	
	First Named Inventor	Dan YANSON		
	Art Unit	2813		
	Examiner Name	Vicki B. BOOKER		
Attorney Docket Number		35832.000130		

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1	YI, H T. ET AL., "Effect of dielectric and semiconductor cap layer combinations in impurity free vacancy disordering of an InGaAs/InGaAsP single quantum well structure", Sae Mulli, Vol. 41, pp. 193-6 (Sept. 2000)	<input type="checkbox"/>
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